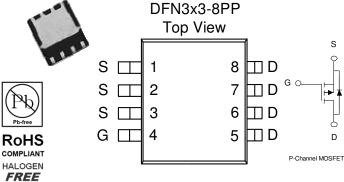
P-Channel 100-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

•	Low $r_{DS(on)}$ provides higher efficiency and
	extends battery life

- Low thermal impedance copper leadframe DFN3x3-8PP saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY					
V _{DS} (V)	$r_{DS(on)} m(\Omega)$	$I_{D}(A)$			
-100	$269 @ V_{GS} = -10V$	-3			
-100	$289 @ V_{GS} = -5.5V$	-2.9			



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)						
Parameter			Maximum	Units		
Drain-Source Voltage			-100	V		
Gate-Source Voltage			±20	V		
Continuous Drain Current ^a	T _A =25°C	Τ_	-3			
Continuous Drain Current	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	ъ	-2.5	A		
Pulsed Drain Current ^b	I_{DM}	±50				
Continuous Source Current (Diode Conduction) ^a	I_S	-2.1	A			
D	$T_A=25^{\circ}C$	P_{D}	3.5	W		
Power Dissipation ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	rD	2.0	l vv		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150	°C			

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Maximum	Units		
a	t <= 10 sec	Ъ	35	°C/W		
Maximum Junction-to-Ambient ^a	Steady State	$R_{\theta JA}$	81	°C/W		

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

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SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Cymbol	Took Oom dikinga	Limits			Unit	
Parameter	Symbol	Test Conditions	Min	Тур	Max	Ullit	
Static	-						
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \text{ uA}$	-1			٧	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±10	μΑ	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -80 \text{ V}, V_{GS} = 0 \text{ V}$			-1		
Zero date voltage Brain ourient	USS	$V_{DS} = -80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-5	μΑ	
On-State Drain Current ^A	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-50			Α	
Duein Course On Besistenes ^A	r	$V_{GS} = -10 \text{ V}, I_{D} = -1 \text{ A}$			269	mΩ	
Drain-Source On-Resistance ^A	r _{DS(on)}	$V_{GS} = -5.5 \text{ V}, I_D = -1 \text{ A}$			289	11122	
Forward Tranconductance ^A	g _{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -1 \text{ A}$		29		S	
Diode Forward Voltage	V_{SD}	$I_{S} = 2.5 \text{ A}, V_{GS} = 0 \text{ V}$		-0.8		٧	
Dynamic ^b	•						
Total Gate Charge	Q_g			8			
Gate-Source Charge	Q_{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -5.5 \text{ V},$ $I_{D} = -1 \text{ A}$		3		nC	
Gate-Drain Charge	Q_{gd}	1D = -1 A		3			
Input Capacitance	C _{iss}			1300			
Output Capacitance	citance C_{oss} V_{DS} =-15V, V_{GS} =0V, f=1MHz			130		pF	
Reverse Transfer Capacitance	C_{rss}			70			
Turn-On Delay Time	t _{d(on)}			5			
Rise Time	t _r	V_{DD} = -15 V, R_L = 6 Ω ,		4		nS	
Turn-Off Delay Time	t _{d(off)}	$I_D = -1 A$, $V_{GEN} = -10 V$		60			
Fall-Time	t _f]		40			

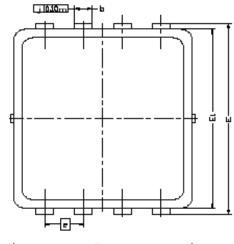
Notes

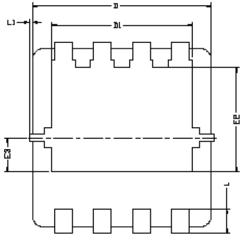
a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.

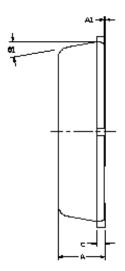
b. Guaranteed by design, not subject to production testing.

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Package Information







DIM.	MIL	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0,700	0'80	0.900	0.0276	0.0315	0.0354	
A1	0.00		0.05	0.000		0.002	
b	0.24	0.30	0.35	0.009	0.012	0.014	
2	0.10	0.152	0.25	0,004	0,006	0.010	
ם	3.00 BSC			٥	118 BS	C	
D1	2.35 B2C			0.093 BSC			
Ε	3,20 BSC			3.20 BSC 0.126 BSC			
E1	3.00 BSC			٥	.118 BS	:C	
E5	1.75 BSC			a.	069 BS	ic o	
E3	0.575 BSC			0.	023 BS	3C	
6	0.65 BSC			Ō.	026 BS	C 2	
Г	0,30	0,40	0,50	0,0118	0.0157	0.0197	
L1			0.100	D		0.004	
9 1	٥٥	10*	12*	0*	10*	12*	